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# 1 Block diagram

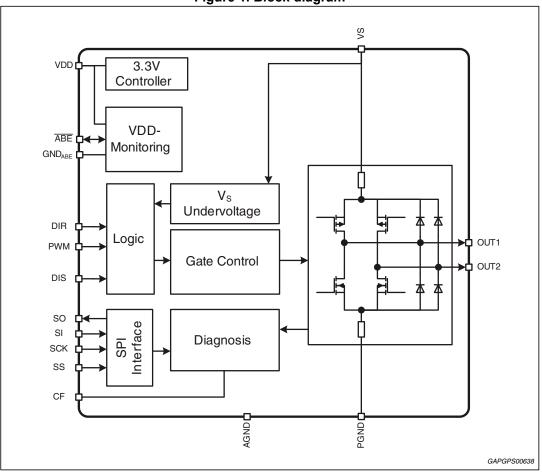
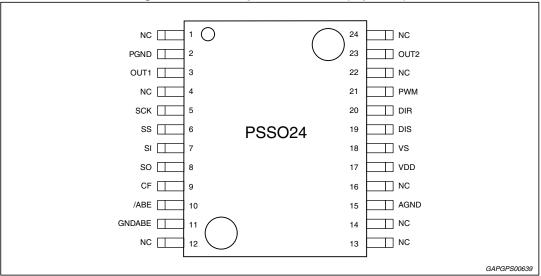
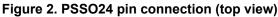


Figure 1. Block diagram

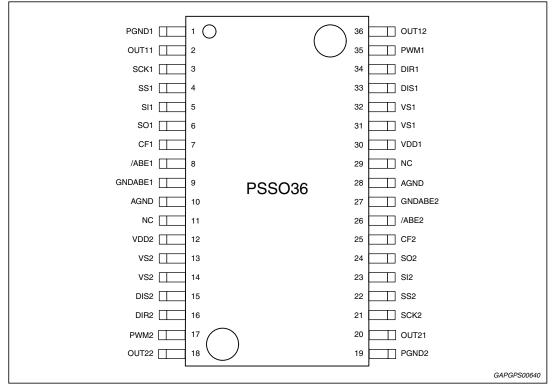


# 2 Pins description





### Figure 3. PSSO36 pin connection (top view)





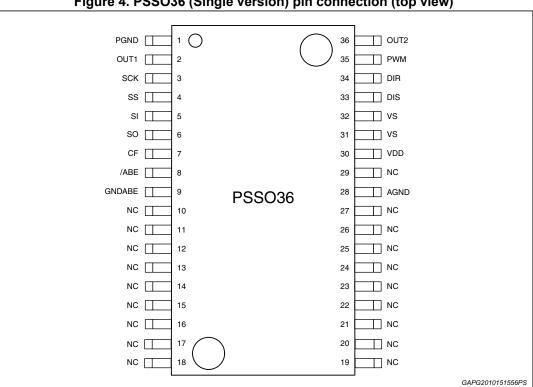


Figure 4. PSSO36 (Single version) pin connection (top view)

#### Pin definitions and functions 2.1

### Table 2. L9959S PSSO24 pin-out

Pin	Symbol	Function		
1, 4, 12, 13, 14, 16, 22, 24	NC	To be connected to GND on PCB.		
2	PGND	Power Ground		
3	OUT1	Bridge output 1 and 2: The bridge outputs are built of a high-side p-channel and a low-side N-channel transistor.		
5	SCK	al clock input: s input controls the internal shift register of the SPI.		
6	SS	Slave Select input: The serial data transfer between the device and the micro controller is enabled by pulling the input SS to low level.		
7	SI	Slave in (Serial data input): The input receives serial data from the microcontroller.		
8	SO	Slave Out (Serial data output): The diagnosis data is available via the SPI through this tristate-output.		



Pin	Symbol	Function		
9	CF	urrent Proportional Feedback output: ne CF pin provides in conjunction with an external resistor an output current, which is oportional to the H-Bridge current.		
10	/ABE	directional Ability/Enable Pin: pen-Drain Output, which is pulled low in case of VDD over- and under-voltage. If the input pulled to low, all output stages are switched off.		
11	GNDABE	Sense Ground for VDD monitoring		
15	AGND	Device Ground. (Connected to Exposed PAD)		
17	VDD	VDD Supply: 5 V Supply		
18	VS	Power supply voltage for power stage outputs (external reverse protection required)		
19	DIS	Disable input: DIS switches OUT1 and OUT2 to tristate.		
20	DIR	Direction input: The DIR pin controls the switch direction of OUT1 and OUT2.		
21	PWM	PWM input: The PWM input switches OUT1 and OUT2.		
23	OUT2	Bridge output 1 and 2: The bridge outputs are built of a high-side p-channel and a low-side N-channel transistor.		
EP	AGND	Exposed Pad: Connected to AGND.		

### Table 2. L9959S PSSO24 pin-out (continued)

### Table 3. L9959T (Two H-Bridge drivers in one package) PSSO36 pin-out

Pin	Symbol	Function		
1	PGND1 <sup>(1)</sup>	Ground: Important: For the capability of driving the full current at the outputs, all ground pins must be externally connected.		
2	OUT11	Bridge output 11, 12, 21, and 22: The bridge outputs are built of a high-side p-channel and a low-side N-channel transistor. The bridge outputs of chip 1 are OUT11 and OUT12, of chip 2 OUT21 and OUT22.		
3	SCK1	Serial clock input: This input controls the internal shift register of the SPI. SCK1 belongs to chip 1 and SCK2 to chip 2.		
4	SS1	Slave Select input: The serial data transfer between the device and the micro controller is enabled by pulling the input SS to low level. SS1 belongs to chip 1 and SS2 to chip 2.		
5	SI1	Slave in (Serial data input):SI1The input receives serial data from the microcontroller.SI1 belongs to chip 1 and SI2 to chip 2.		
6	SO1	Slave Out (Serial data output): The diagnosis data is available via the SPI through this tristate-output. SO1 belongs to chip 1 and SO2 to chip 2.		



Pin	in Symbol Function				
7	CF1	Current Proportional Feedback output: The CF pin provides in conjunction with an external resistor an output current, which is proportional to the H-Bridge current. CF1 belongs to OUT11 and OUT12, CF2 to OUT21 and OUT22.			
8	/ABE1	Bidirectional Ability/Enable Pin 1: Open-Drain Output, which is pulled low in case of VDD over- and under-voltage. If the input is pulled to low, all output stages are switched off. /ABE1 belongs to chip 1.			
9	GNDABE1	Sense Ground for VDD monitoring			
10, 28	AGND	Device Ground. (Connected to Exposed PAD)			
11, 29	NC	To be connected to GND on PCB.			
12	VDD2 <sup>(2)</sup>	VDD Supply: 5V Supply.			
13, 14,	VS2 <sup>(3)</sup>	Power supply voltage for power stage outputs (external reverse protection required): Important: For the capability of driving the full current at the outputs all pins of VS must be externally connected.			
15	DIS2	Disable input 2: DIS2 switches OUT21 and OUT22 to tristate.			
16	DIR2	Direction input 2: DIR2 pin controls the switch direction of OUT21 and OUT22.			
17	PWM2	PWM input 2: PWM1 input switches OUT21 and OUT22.			
18	OUT22	Bridge output 11, 12, 21, and 22: The bridge outputs are built of a high-side p-channel and a low-side N-channel transistor. The bridge outputs of chip 1 are OUT11 and OUT12, of chip 2 OUT21 and OUT22.			
19	PGND2 <sup>(1)</sup>	Ground: Important: For the capability of driving the full current at the outputs, all ground pins must be externally connected.			
20	OUT21	Bridge output 11, 12, 21, and 22: The bridge outputs are built of a high-side p-channel and a low-side N-channel transistor. The bridge outputs of chip 1 are OUT11 and OUT12, of chip 2 OUT21 and OUT22.			
21	SCK2	Serial clock input: This input controls the internal shift register of the SPI. SCK1 belongs to chip 1 and SCK2 to chip 2.			
22	SS2	Slave Select input: The serial data transfer between the device and the micro controller is enabled by pulling the input SS to low level. SS1 belongs to chip 1 and SS2 to chip 2.			
23	SI2	Slave in (Serial data input): The input receives serial data from the microcontroller. SI1 belongs to chip 1 and SI2 to chip 2.			
24	SO2	Slave Out (Serial data output): The diagnosis data is available via the SPI through this tristate-output. SO1 belongs to chip 1 and SO2 to chip 2.			

### Table 3. L9959T (Two H-Bridge drivers in one package) PSSO36 pin-out (continued)

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25	CF2	Current Proportional Feedback output:	
	012	urrent Proportional Feedback output: he CF pin provides in conjunction with an external resistor an output current, which is roportional to the H-Bridge current. CF1 belongs to OUT11 and OUT12, CF2 to OUT21 nd OUT22.	
26	/ABE2	Bidirectional Ability/Enable Pin 2: Open-Drain Output, which is pulled low in case of VDD over- and under-voltage. If the input is pulled to low, all output stages are switched off. /ABE2 belongs to chip 2.	
27	GNDABE2	Sense Ground for VDD monitoring	
30	VDD1 <sup>(2)</sup>	VDD Supply: 5V Supply.	
31, 32	VS1 <sup>(3)</sup>	Power supply voltage for power stage outputs (external reverse protection required): Important: For the capability of driving the full current at the outputs all pins of VS must be externally connected.	
33	DIS1	Disable input 1: DIS1 switches OUT11 and OUT12 to tristate	
34	DIR1	Direction input 1: DIR1 pin controls the switch direction of OUT11 and OUT12.	
35	PWM1	PWM input 1: PWM1 input switches OUT11 and OUT12.	
36	OUT12	Bridge output 11, 12, 21, and 22: The bridge outputs are built of a high-side p-channel and a low-side N-channel transistor. The bridge outputs of chip 1 are OUT11 and OUT12, of chip 2 OUT21 and OUT22.	
EP	AGND <sup>(4)</sup>	Exposed PAD: connected to AGND	

Table 3. L9959T (	(Two H-Bridge	drivore in ono	nackado)	Deeuse	nin_out /	(continued)	
	(IWO II-DIIUge		package,	1 00000	pin-out (	(commueu)	

1. Pins 1 is referred to die 1, whereas 19 is referred to die 2.

2. Pins 12 is referred to die 2, whereas 30 is referred to die 1.

3. Pins 13 and 14 are referred to die 2, whereas pins 31 and 32 are referred to die 1.

4. Pins 10 is referred to die 2, whereas 28 is referred to die 1.



	Table 4. L9959U (Single version in PSSO36) pin out					
Pin	Symbol	Function				
1	PGND	Ground: Important: For the capability of driving the full current at the outputs, all ground pins must be externally connected.				
2	OUT1	The bridge outputs are built of a high-side p-channel and a low-side N-channel transistor.				
3	SCK	Serial clock input: This input controls the internal shift register of the SPI.				
7	CF	Current Proportional Feedback output: The CF pin provides in conjunction with an external resistor an output current, which is proportional to the H-Bridge current				
8	/ABE	Bidirectional Ability/Enable Pin: Open-Drain Output, which is pulled low in case of VDD over- and under-voltage. If the input is pulled to low, all output stages are switched off.				
9	GNDABE	Sense Ground for VDD monitoring				
10,11, 12,13, 14,15, 16,17, 18,19, 20,21, 22,23, 24,25, 26,27, 29	NC	To be connected to GND on PCB.				
28	AGND	Device Ground. (Connected to Exposed PAD)				
30	VDD	VDD Supply: 5 V Supply.				
31, 32	VS1	Power supply voltage for power stage outputs (external reverse protection required): Important: For the capability of driving the full current at the outputs all pins of VS must be externally connected.				
33	DIS	Disable input : DIS switches OUT1 and OUT2 to tristate				
34	DIR	Direction input: DIR pin controls the switch direction of OUT1 and OUT2.				
35	PWM	PWM input: PWM input switches OUT1 and OUT2.				
36	OUT2	The bridge outputs are built of a high-side p-channel and a low-side N-channel transistor.				

Table 4. L9959U	(Single version in	PSSO36)	nin out
	Comple version in	1100000,	pin out



# 3 Electrical specifications

## 3.1 Absolute maximum ratings

Warning: Stressing the device above the rating listed in the "Absolute maximum ratings" table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE program and other relevant quality document.

Symbol	Parameter / Test condition	Value [DC Voltage]	Unit				
V <sub>VS</sub>	DC supply voltage The device is able to sustain load dump as specified in the ISO16750 documentation	-1.0 to +40	V				
V <sub>VDD</sub> Stabilized supply voltage, logic supply		-0.3 to 18	V				
C <sub>F</sub> <sup>(1)</sup>	Current feedback output	-0.3 to 18	V				
V <sub>SI</sub> , V <sub>SCK</sub> , V <sub>SS</sub> , V <sub>SO</sub> , V <sub>DIR</sub> , V <sub>PWM</sub> , V <sub>DIS</sub>	Logic input / output voltage range	-0.3 to 18	V				
V <sub>OUTn</sub>	Output voltage (n = 1,2 or 11,12,21,22); V <sub>OUTn</sub> < V <sub>S</sub> + 1 V	-1.0 to 40	V				
	Dynamic pulse / t < 500ms; $V_{OUTn} < V_{S} + 2 V$	-2.0 to 40	V				
т	Operating junction temperature	-40 to 150	°C				
Тj	Dynamic junction temperature (1000hrs)	150 to 175	°C				
T <sub>stg</sub>	Storage temperature	-55 to 150	°C				

1. It is withstood at  $V_S$  = 18 V

# 3.2 ESD protection

### Table 6. ESD protection

Parameter	Value	Unit
All pins versus ground group (AGND, PGND1, PGND2, GND_ABE1, GND_ABE2)	±2 <sup>(1)</sup>	kV
VS pin, Power Output Pins: OUT1, OUT2 or OUT11, OUT12, OUT21, OUT22 versus ground group (AGND, PGND1, PGND2, GND_ABE1, GND_ABE2)	±4 <sup>(2)</sup>	kV

1. HBM according to MIL 883C, Method 3015.7 or EIA/JESD22-A114-A.

2. HBM with all unzipped pins grounded.



# 3.3 Thermal data

Symbol	Parameter	Value	Unit
R <sub>thj-case</sub>	Thermal resistance junction-to-case (max) for L9959S, L9959T	2.0	°C/W

### Table 7. Thermal data

# 3.4 Electrical characteristics

The voltages are referred to ground and currents are assumed positive, when the current flows into the pin. 4.5 V  $\leq$  V<sub>S</sub>  $\leq$  18 V, 4.5 V  $\leq$  V<sub>DD</sub>  $\leq$  5.5 V; all outputs open; T<sub>j</sub> = -40 °C to 150 °C, unless otherwise specified.

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
V <sub>S</sub>	Operating voltage range	-	4.5	-	28	V
		$V_{DD} = 5 V; V_S = 5 V and V_S = 18 V;$ Bridge disabled	-	-	5	mA
I <sub>VS</sub>	V <sub>S</sub> current consumption in active mode	$\label{eq:VD} \begin{array}{l} V_{DD} = 5 \ V; \ V_S = 5 \ V \ \text{and} \\ V_S = 18 \ V; \ f_{OUT} = 2 \ \text{kHz}; \\ I_{OUT} = 0 \ \text{A} \end{array}$	-	-	6	mA
		$\label{eq:VD} \begin{split} V_{DD} &= 5 \text{ V};  \text{V}_{\text{S}} = 5  \text{V} \text{ and} \\ V_{\text{S}} &= 18  \text{V};  \text{f}_{\text{OUT}} = 10  \text{kHz}; \\ \text{I}_{\text{OUT}} &= 0  \text{A} \end{split}$	-	-	14	mA
		V <sub>DD</sub> = 5 V; V <sub>S</sub> = 28 V; f <sub>OUT</sub> = 10 kHz; I <sub>OUT</sub> = 0 A	-	-	14	mA
I <sub>VS(stby)</sub>	V <sub>S</sub> current consumption in passive mode	V <sub>DD</sub> = 0 V	0	-	2.5	mA
V <sub>VS_slew</sub> <sup>(1)</sup>	Slew rate on V <sub>S</sub>	-	-	-	100	V/µs
V <sub>VS_slew</sub> <sup>(2)</sup>	Slew rate on V <sub>S</sub>	-	-	-	20	V/µs
V <sub>DD</sub>	Operating voltage range	-	4.5	-	5.5	V
I <sub>VDD</sub>	V <sub>DD</sub> supply current	V <sub>S</sub> = 18 V; V <sub>DD</sub> = 5 V	_	-	10	mA

### Table 8. Supply

1. No change of parameters for VDD-monitoring and in SPI logic

2. No change of parameters

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Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
V <sub>DDRES</sub>	Reset active threshold	-	2.8	-	3.4	V
V <sub>DDPOR</sub>	Power-on reset threshold	-	3.3	-	4	V
V <sub>DDPORHYS</sub>	Power-on reset hysteresis	-	-	600	-	mV
t <sub>POR</sub>	Power-on reset extension time	-	-	-	1	ms

### Table 9. Power-on reset

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
V <sub>DD</sub>	V <sub>DD</sub> monitoring voltage range	-	V <sub>DDPOR</sub>	-	18	V
V <sub>DD_THL</sub>	Under voltage threshold	V <sub>S</sub> = 0 V	4.2	-	4.5	V
V <sub>DD_THH</sub>	Over voltage threshold	V <sub>S</sub> = 0 V	5.25	-	5.5	V
t <sub>FIL_OFF</sub>	Switch-off filtering time	Guaranteed by scan.	60	-	135	μs
t <sub>FIL_ON</sub>	Switch-on filtering time	Guaranteeu by scan.	60	-	135	μs
V <sub>TEST_THL</sub>	Under voltage test threshold	-	5.25	-	5.5	V
V <sub>TEST_THH</sub>	Over voltage test threshold	-	4.2	-	4.4	V
V <sub>DD_MR</sub>	Full V <sub>DD</sub> supply range	-	-0.3	-	18	V
V <sub>DD_SLEW</sub>	V <sub>DD</sub> slew	-		-	500	mV/µs
ΔV <sub>DD_THX</sub>	Threshold ( $V_{DD_THH}, V_{DD_THL}$ ) shift during vs. inverse current	-	-0.1	-	0.1	V
V <sub>ABE_INL</sub>	/ABE input low-level	-	-0.3	-	1.65	V
V <sub>ABE_INH</sub>	/ABE input high-level	-	3.15	-	18	V
V <sub>ABE_INHY</sub> s	/ABE input hysteresis	-	0.2	-	1.0	V
		0 V < V <sub>ABE</sub> < 1.5 V	0	-	60	μA
I <sub>ABE_IN</sub>	/ABE input pull-down current	V <sub>ABE</sub> = 2.1 V, 5 V, 18 V; V <sub>S</sub> = 18 V; V <sub>DD</sub> = 5 V, 18 V	20	40	60	μΑ
V <sub>ABE_OUTL</sub>	/ABE output low voltage	2.5 V < V <sub>DD</sub> < V <sub>DD_THL</sub> ; I <sub>ABE_OUTL</sub> < 2.5 mĀ	0	-	1.0	V
V <sub>ABE_OUTL</sub>	/ABE output low voltage	V <sub>DD_THH</sub> < V <sub>DD</sub> < 18V; I <sub>ABE_OUTL</sub> < 7.5 mA	0	-	1.2	V
V <sub>ABE_OUTL</sub>	/ABE output passive low voltage	-	0	-	1.2	V
ΔI <sub>ABE</sub>	I <sub>ABE</sub> Change during vs. inverse current	-	-100	-	100	μA

## Table 10. V<sub>DD</sub> monitoring



Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit	
V <sub>UV_OFF</sub>	VS UV threshold	VS decreasing	3.1	3.8	4.5	V	
V <sub>UV_ON</sub>	VS UV threshold	VS increasing	3.3	4.0	4.7	V	
V <sub>UV_HYS</sub>	VS UV hysteresis	V <sub>UV_ON</sub> - V <sub>UV_OFF</sub>	0.1	-	1	V	
t <sub>FUV</sub>	VS UV detection time	-	-	-	1.5	μs	

Table 11. Undervoltage shutdown

# 3.5 Outputs OUT1 and OUT2

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit	
r <sub>ONVS</sub> OUT1,2	On-resistance to supply	V <sub>DD</sub> = 5 V; V <sub>S</sub> = 10 V, I <sub>OUT1,2</sub> = 3 A	-	-	315	mΩ	
r <sub>ONGND</sub> OUT1,2	On-resistance to PGND	V <sub>DD</sub> = 5 V; V <sub>S</sub> = 10 V, I <sub>OUT1,2</sub> = 3 A	-	-	225	mΩ	
Switched-off output current of	V <sub>DD</sub> = 5 V; V <sub>S</sub> = 13 V; V <sub>OUT</sub> = 0 V	-200	-	-	μA		
	$V_{DD}$ = 5 V; $V_{S}$ = 13 V; $V_{OUT}$ = $V_{S}$	-	-	200	μA		

### Table 12. On-resistance $(4.5 \text{ V} < \text{V}_{\text{S}} < 28 \text{ V})$

### Table 13. Power output switching times (8 V < $V_S$ < 18 V)

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
t <sub>d ON</sub>	Output delay time driver on	-	-	-	6	μs
t <sub>d OFF</sub>	Output delay time driver off	-	-	-	20	μs
t <sub>d dis</sub> <sup>(1)</sup>	Disable delay time		-	-	12.5	μs
t <sub>d pwon</sub>	Power-on delay time	Guaranteed through scan.	-	-	1	ms
t <sub>d en</sub>	Enable delay time		-	-	50	μs
dl <sub>OUT</sub> /dt	Current slew rate	-	-	1.6		A/µs
dV <sub>OUTHS</sub> /dt	Output rise/fall slew-rate high-side slow selected with bit SR = 0 fast selected with bit SR = 1	$V_{DD}$ = 5 V; V <sub>S</sub> = 14 V R <sub>LOAD1,2</sub> = 2.6 Ω (8 V <sub>S</sub> ), 6 Ω (18 V <sub>S</sub> )	0.975 2.8	-	2.7 8	V/µs
dV <sub>rOUTLS</sub> /dt	Output rise slew-rate low-side valid only after the toggling of DIR input		0.975	-	2.7	V/µs
dV <sub>fOUTLS</sub> /dt	Output fall slew-rate low-side		2.5	4	8	V/µs
f <sub>pwmmax</sub>	PWM input frequency	-	-	-	11	kHz

1. Driven by /ABE or DIS input.

The slew-rates (dV<sub>OUT</sub>/dt1) are defined by dV (voltage difference 20% - 80%) divided by the rise-/fall times (t<sub>r</sub>/t<sub>f</sub> see Figure 6: Output rise and fall times).



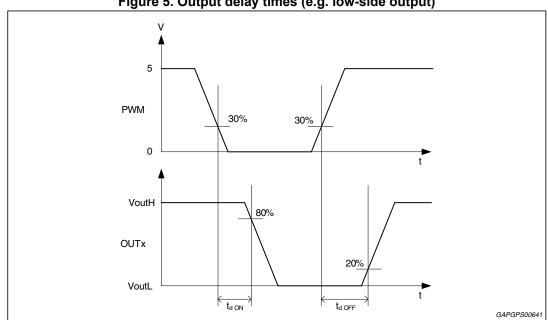
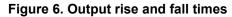


Figure 5. Output delay times (e.g. low-side output)



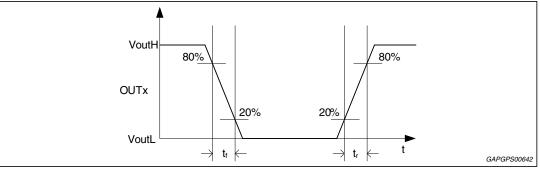
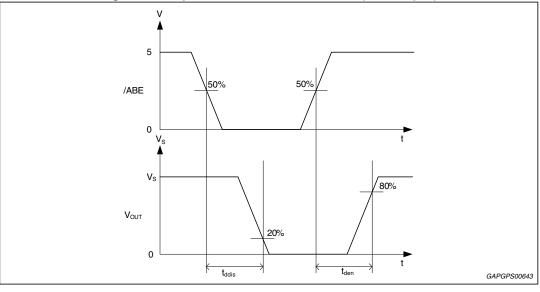


Figure 7. Output disable and enable time (/ABE Input)





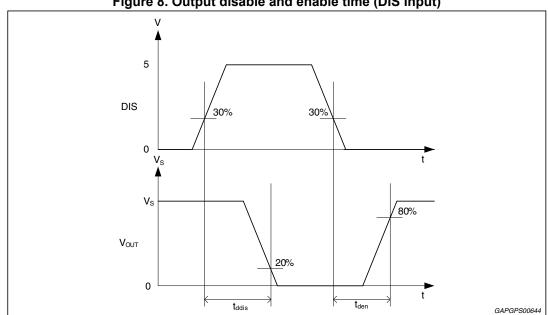


Figure 8. Output disable and enable time (DIS Input)

### Table 14. Current feedback (CF)

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
V <sub>CF</sub> <sup>(1)</sup>	CF voltage range	$V_{S} > 6.5 V$ , OUTx = 0 A, T <sub>J</sub> = -40 °C; Current level 2,3,4	0.01	0.05	0.20	V
		V <sub>S</sub> > 6.5 V, OUTx = 250mA, T <sub>J</sub> = 130 °C; Current level 2,3,4	0.04	0.275	0.5	V
		$V_{S} > 6.5 V$ , OUTx = 0.4 * $I_{clx}$ , $T_{J} = 130 °C$ ; Current level 2,3,4	1.71	1.80	1.89	V
		$V_S > 6.5 V$ , OUTx = I <sub>clx</sub> T <sub>J</sub> = -40°C to 150°C; Current level 2,3,4	3.82	4.5	5.18	V
R <sub>CF</sub> <sup>(2)</sup>	CF resistor range	-	-	5.1	-	kΩ
I <sub>OFFSET</sub>	CF offset current	-	_	10	_	μA

1. Measured at a 5.1k resistor between CF and GND ( $R_{CF}$ ). Levels see *Table 34* Current Level (CONFIG\_REG).

2. Defined by design, not tested.

Note: This signal has an individual error ±5 % in each of the three currents levels, at trimming temperature of 130 °C. Additional an individual error ±10 % in each of the three current levels over temperature and aging. So the maximum error is of ±15 % in each of the three current levels. The offset and the gain errors may be different in each current level. The adjustment is done at 130 °C and compensates the error corresponding to 0.4 \* Iclx



	Table 15. Current limiting							
Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit		
$  _{CL2} ^{(1)}$	Current limit <sub>2</sub>		4.25	5	5.75	А		
<sub>CL3</sub>   <sup>(1)</sup>	Current limit <sub>3</sub>	R <sub>CF</sub> = 5.1 kΩ	5.6	6.6	7.6	A		
I <sub>CL4</sub>   <sup>(1)</sup>	Current limit <sub>4</sub>		7.3	8.6	9.9	A		
<sub>HYS2-4</sub>   <sup>(1)</sup>	Current limit hysteresis <sub>1</sub>	-	-5% ICL <sub>2-4</sub>	-	-10% ICL <sub>2-4</sub>	А		
t <sub>b</sub>	Blanking time	Guaranteed through	8	11	15	μs		
t <sub>trans</sub>	Time between two transient	scan.	90	-	130	μs		

### Table 15. Current limiting

Programmable current levels see *Table 34* Current Level (CONFIG\_REG). Measured using a 5.1 kΩ resistor between CF and GND (R<sub>CF</sub>).

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
I <sub>OC2_LS</sub>   <sup>(1)</sup>	Low side over current threshold <sub>2</sub>	V <sub>DD</sub> = 5 V	4.9	-	8.2	А
I <sub>OC3_LS</sub>   <sup>(1)</sup>	Low side over current threshold <sub>3</sub>	V <sub>DD</sub> = 5 V	6.7	-	11.1	А
I <sub>OC4_LS</sub>   <sup>(1)</sup>	Low side over current threshold <sub>4</sub>	V <sub>DD</sub> = 5 V	8.4	-	14	А
II <sub>OC2_HS</sub> I <sup>(1)</sup>	High side over current threshold <sub>2</sub>	V <sub>DD</sub> = 5 V	5.5	-	9.2	А
I <sub>OC3_HS</sub>   <sup>(1)</sup>	High side over current threshold <sub>3</sub>	V <sub>DD</sub> = 5 V	6.9	-	11.5	A
I <sub>OC4_HS</sub>   <sup>(1)</sup>	High side over current threshold <sub>4</sub>	V <sub>DD</sub> = 5 V	8.6	-	14.4	А
I <sub>TRACK-2</sub> <sup>(2)</sup>	<sub>OC2</sub>   -    <sub>CL2</sub>	V <sub>DD</sub> = 5 V	0.4	-	5.5	A
I <sub>TRACK-3</sub> <sup>(2)</sup>	<sub>OC3</sub>   -    <sub>CL3</sub>	V <sub>DD</sub> = 5 V	0.4	-	5.5	А
I <sub>TRACK-4</sub> <sup>(2)</sup>	<sub>OC4</sub>   -    <sub>CL4</sub>	V <sub>DD</sub> = 5 V	0.4	-	5.5	A
t <sub>DF</sub>	Delay time for fault detection	guaranteed by design	1	2	4.5	μs
t <sub>DF_off</sub>	Switch-off delay time	-			6	μs
t <sub>DF_del</sub>	Delayed switch-off time	-	20		200	μs
t <sub>SC</sub>	Short-circuit detection	guaranteed through scan	292	350	413	μs

## Table 16. Over-current detection (8 V < $V_S$ < 18 V)

1. Programmable current levels see Table 34 Current Level (CONFIG\_REG).

2. Tracking values are referred for both LS and HS.



Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
R <sub>OL</sub>	Open-load detection threshold	-	5	-	50	kΩ
t <sub>DIAGOL</sub>	Open-load diagnosis enable delay		100	-	150	ms
t <sub>DIAGOL1</sub>	Open-load diagnosis filter time <sub>1</sub>	Guaranteed through scan.	2.4	-	3.6	ms
t <sub>DIAGOL2</sub>	Open-load diagnosis filter time <sub>2</sub>		200	-	300	μs
V <sub>out1_OFF</sub>	Out1 voltage regulator	-	1.67	-	1.97	V

Table 17. Open-load detection

Note: If the value of the connected load is below  $5 k\Omega$  no Open Load is detected; whereas if the value of the connected load is more than  $50 k\Omega$ , Open Load is detected. If the load is in the range between (5 to 50)  $k\Omega$ , the Open Load diagnosis could be not reliable.

Table 18. Retest delay							
Symbol	Parameter         Test condition         Min.         Typ.         Max.						
t <sub>delay retest</sub>	Retest delay for failures: SCB, SCG, SCL	Guaranteed through scan.	290	350	410	μs	

# 3.6 Temperature dependent current reduction

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
I <sub>L_TSD</sub>	Current limit at T <sub>SD</sub>	-	1.4	2.5	3.6	A
T <sub>ILR</sub>	Start of temperature dependent current reduction	-	150	165	-	°C
T <sub>SD</sub>	Thermal shut-down	-	175	-	-	°C
T <sub>SD</sub> -T <sub>ILR</sub>	Range of temperature dependent current reduction	-	20	25	30	°C
T <sub>fTSD</sub>	Thermo-shut-down detection filter time	Guaranteed through scan.	6	-	18	μs

### Table 19. Temperature dependent current reduction

Note: see also Figure 17: Temperature dependent current reduction.

# 3.7 Free-wheeling diodes

### Table 20. Free-wheel diodes

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
U <sub>D</sub>	Free-wheeling diode forward voltage	I <sub>OUT</sub> = 3 A	-	-	2	V
T <sub>it</sub> <sup>(1)</sup>	Free-wheeling diode reverse recovery time	-	-	-	100	ns

1. Not subject to production test; specified by design.





# 3.8 SPI / logic electrical characteristics

The voltages are referred to ground and currents are assumed positive, when the current flows into the pin. 4.5 V  $\leq$  V<sub>S</sub>  $\leq$  18 V, 4.5 V  $\leq$  V<sub>CC</sub>  $\leq$  5.5 V; all outputs open; T<sub>j</sub> = -40 °C to 150 °C, unless otherwise specified.

Symbol	Parameter	Test condition	Min	Тур	Max	Unit
Inputs: SI,	SS, SCK DIR, PWM		-			
V <sub>IL</sub>	Input voltage low-level	V <sub>DD</sub> = 5 V	-0.3	-	0.75	V
V <sub>IH</sub>	Input voltage high-level	V <sub>DD</sub> = 5 V	1.75	-	VDD+0.3	V
V <sub>IHYS</sub>	Input hysteresis	V <sub>DD</sub> = 5 V	0.2	-	1.0	V
R <sub>PUin</sub>	Input pull-up resistor	V <sub>DD</sub> = 5 V	50	-	250	kΩ
I <sub>INx</sub>	PWM, DIR input current	V <sub>INx</sub> > 3.0V	-5	-	5	μA
C <sub>Slin</sub> <sup>(1)</sup>	SI input capacitance	-	-	-	10	pF
C <sub>SCKin</sub> <sup>(1)</sup>	SCK input capacitance	-	-	-	10	pF
C <sub>SSin</sub> <sup>(1)</sup>	SS Input Capacitance	-	-	-	15	pF
C <sub>DIR,PWMin</sub>	DIR, PWM input capacitance	-	-	-	20	pF
Input: DIS						
R <sub>DISPU</sub>	Pull-up resistor	0 V < V <sub>DIS</sub> < 2.1 V	10	-	45	kΩ
I <sub>DISx</sub>	DIS input current	V <sub>DIS</sub> > 3 V	-5	-	5	μA
C <sub>DIS in</sub> <sup>(1)</sup>	DIS input capacitance	-	-	-	20	pF
t <sub>DIS</sub>	DIS pulse width	-	0.5	1	1.5	μs
Input pin d	isturbance (SI, SS, SCK DIR, F	PWM,DIS)	· ·		- <b>-</b>	
ΔVx_HL	Change of $V_{IH}$ and $V_{IL}$ during inverse current on $V_{\rm S}$		-0.1	-	0.1	V
ΔISx	Change of input current of SPI input pins during inverse current on $\mathrm{V}_{\mathrm{S}}$	Not subjected to test in production.	-100	-	100	μA
Output: SO			•			
V <sub>SOL</sub>	Output voltage low level	I <sub>OL</sub> = 2 mA,	0	-	0.4	V
V <sub>SOH</sub>	Output voltage high level	I <sub>OH</sub> = -2 mA	VDD-0.5	-	VDD	V
SR <sub>SO</sub> <sup>(1)</sup>	Slew rate	C <sub>LOAD</sub> = 200 pF	0.3	-	0.6	V/ns
I <sub>SOLK</sub>	Tristate leakage current	V <sub>SS</sub> = V <sub>DD</sub>	-10	-	10	μA
$C_{SO out}^{(1)}$	SO output capacitance	-	-	-	10	pF
Output pin	disturbance (SO)				_,I	
$\Delta I_{SOLK}$	Change of I <sub>SOLK</sub> during inverse Current on VS	-	-100	-	100	μA

### Table 21. Inputs: SI, SS, SCK, DIR, DIS and PWM; Output: SO

1. Not measured in production test. Parameter guaranteed by design.

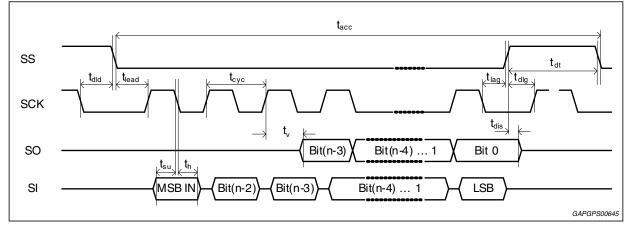


### **Electrical specifications**

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
-	Cycle time		490			ns
t <sub>cyc</sub>		-		-	-	-
t <sub>lead</sub>	Enable lead time	-	300	-	-	ns
t <sub>lag</sub>	Enable lag time	-	150	-	-	ns
		SCK = 2 V; SO = 0.2 V; C <sub>L</sub> = 40 pF	40	-	-	ns
t <sub>v</sub>	t <sub>v</sub> Data valid	SCK = 2 V; SO = 0.2 V; C <sub>L</sub> = 200 pF	150	-	-	ns
		SCK = 2 V; SO = 0.2 V; C <sub>L</sub> = 350 pF	230	-	-	ns
t <sub>su</sub>	Data setup time	-	40	-	-	ns
t <sub>h</sub>	Data hold time	-	40	-	-	ns
t <sub>dis</sub>	Disable time	-	0	-	100	ns
t <sub>dt</sub>	Transfer delay	-	300	-	-	ns
t <sub>dld</sub>	Disable lead time	-	250	-	-	ns
t <sub>dlg</sub>	Disable lag time	-	250	-	-	ns
t <sub>acc</sub>	Access time	-	8.35	-	-	μs

### Table 22. Dynamic characteristics

## Figure 9. SPI timing information





# 4 Application information

## 4.1 Power stage switching behavior

The L9959 output stages can either be controlled by the pins PWM and DIR or by their corresponding SPI registers (SPWM and SDIR: see *Table 33* in Configuration Register (CONFIG\_REG)). The SPI bit MUX in the configuration register (CONFIG\_REG) is used to define the driving control strategy of the H-bridge. If the power stages are disabled by /ABE or DIS, this bit is reset and the pins PWM and DIR control the outputs.

The active free-wheeling, in which the body diode is actively shorted by its associated Power-MOS, can be disabled by the bit **FW** in the configuration register (CONFIG\_REG). By default, active free-wheeling is enabled.

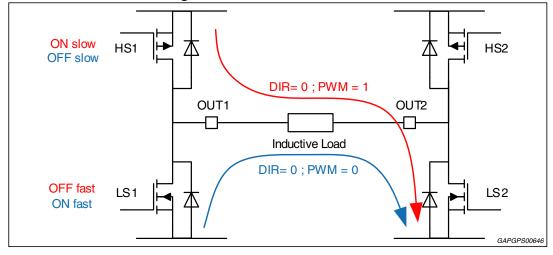
The device minimizes electro-magnetic emission by switching the high-side and low-side drivers in a special sequence. Two cases are distinguished: The PWM-mode, during which the current direction does not change and the direction switches using the DIR, which changes the current direction (see *Figure 10*, *Figure 12* and *Figure 13*).

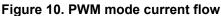
## 4.1.1 PWM mode (same current direction)

The PWM input pin switches the high-/low-side output of the half-bridge, which is selected by the DIR pin.

DIR = '0': OUT1 is switched, DIR = '1': OUT2 is switched.

PWM = '0': Switched low-side is on, PWM = '1': Switched high-side is on.







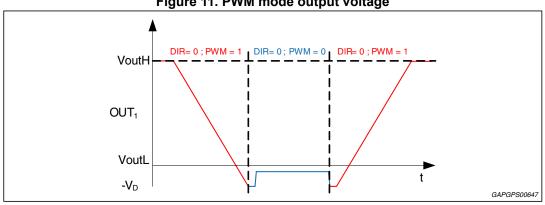


Figure 11. PWM mode output voltage

During PWM mode the high-side (e.g. Figure 10 HS1) output is switched off with a slow slew rate until it is off and the low-side body-diode has taken over the entire current (passive freewheeling). Then the associated low-side transistor (e.g. Figure 10 LS1) is turned on with a fast slope to reduce the voltage across the device and to minimize the power.

The output is pulled to high voltage, by first turning off the low-side driver with a fast slew rate and, after it is off, the high-side driver is switched on by a slow one (e.g. Figure 10 LS1, HS1).

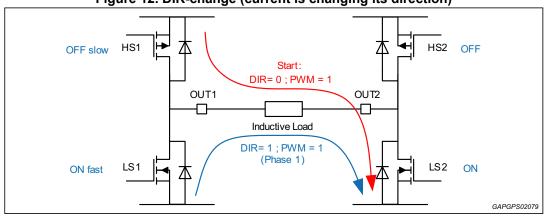
This assures, that the voltage and current change over the body diode is done smoothly, reducing the electromagnetic emission.

#### 4.1.2 **DIR-change mode**

The first part of the sequence is identical to the PWM-mode (s.a.). After this has been finished and the associated low-side driver is on (e.g. Figure 12 LS1), in phase 1 the other low-side driver is turned on (e.g Figure 12 LS2) to enter passive freewheeling phase. Then in phase 2 the low-side output of OUT2 is switched-off slowly and the current through the load is taken over by the body-diode of the high-side (e.g. Figure 13 HS2).

Depending on the inductance of the load, the current vanishes more or less guickly. After the low-side driver is turned off, the high-side is switched on with a slow slew-rate.

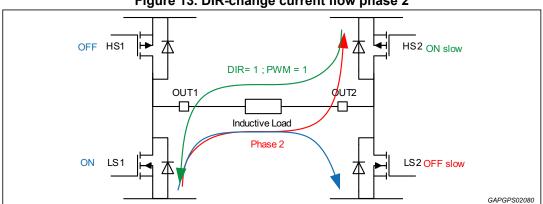
This assures, that direction switch occurs while the current over the load has vanished, which reduces the electromagnetic emission.

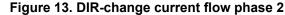


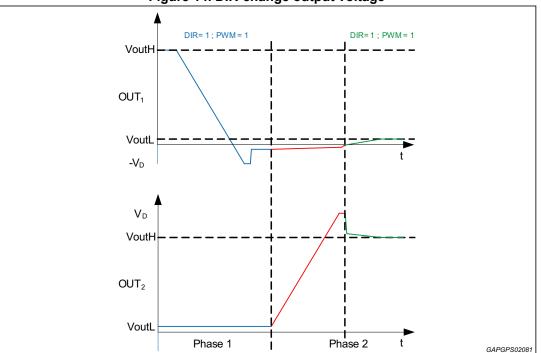


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### Figure 14. DIR-change output voltage

#### 4.2 Protection and monitoring

A set of failure as Short-circuit to Ground (SCG), Short-circuit to battery (SCB) and Shortcircuit to load (SCL) errors (SBC, SCG, SCL) are confirmed after their occurrence by accessing the error condition after time  $t_{delay\_retest}$  a second time. Only after the error is confirmed, it is entered into the diagnosis register 1 (DIA\_REG1), and the device is disabled and no further diagnosis is run.

The device can be enabled again by the following actions: Power-on reset, disabling and enabling the device using the pins /ABE or DIS (e.g. disabling - enabling sequence). The diagnosis registers can be cleared by sending a reset command by SPI (STATCON\_REG) to either diagnosis register 1 (DIA\_REG1) or 2 (DIA\_REG2). The bit1 (Reset) of the CONFIG REG if forced to zero resets both the device registers configuration and diagnosis registers to default but is not able to restart the device. In order to restart IC it is necessary



to force a transition **LOW/HIGH/LOW** on DIS pin or a transition **HIGH/LOW/HIGH** on /ABE pin.

The errors in the diagnosis register 1 (DIA\_REG1) are transferred to the diagnosis register 2 by setting the bit DIACLR1 in the status and configuration register (STATCON\_REG) or by using the enabling -disabling sequence on /ABE or DIS. This will also clear the diagnosis register 1.

### 4.2.1 Current feedback

A feedback current signal is provided at pin CF (Current Feedback). This current is proportional to the current in the H-Bridge, but does not change its direction. It is measured in the low-side transistor, which is not switched by PWM. This is determined by the input DIR or the SDIR register respectively. Therefore, the direction of the current can be seen from this direction signal.

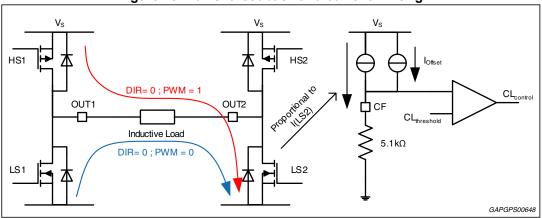
One current sense monitoring circuit is present and it is connected to the output of the active LS driver (DIR change mode).

After the DIR transition, the LSx reference output is switched only in the phase in which both LS drivers are active for recirculation.

In the time-frame between HS turn-off and the start of active freewheeling, (including dead time and passive freewheeling), the current sense monitors the current flowing in the previous active LS driver.

This time-frame is not fixed but adaptative to real operative conditions (battery and selected slew rate mode).

In *Table 14: Current feedback (CF)* the CF behavior over an external resistor of 5.1k Ohm is specified. The current out of CF consists of a static offset current and a current proportional to the current in the select low-side transistor. The voltage at pin CF scales with the resistor at this pin.





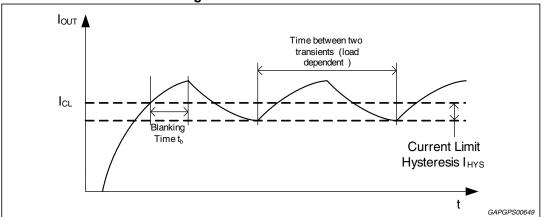
*Figure 15* Current Feedback and Current Limiting shows the current feedback in case the OUT1 is controlled by PWM (DIR = 0). In this case, the current is measured through low-side 2. If the direction is inverted, the current is measured through low-side 1.



#### 4.2.2 **Current limitation**

The H-Bridge output current can be limited to three different values (see Table 15: Current *limiting*). If the current reaches the current limiting threshold ICL, the output driver is switched off after the blanking time  $t_b$ , and switched on again after the current dropped below the lower current limit hysteresis threshold  $(I_{CL} - I_{HYS})$ . The current limiting thresholds can be adjusted using the resistor at pin CF. The values in Table 15 refer to a 5.1k Ohm external resistor. The current limiting threshold can be calculated by (4.5V/R<sub>CF</sub> - $I_{OFFSET}$ ) \* ( $I_{CLx}$ \*5.1k/4.45V) from *Table 15* and  $I_{OFFSET}$  =10µA (typical).  $R_{CF}$  is the resistor used at pin CF.

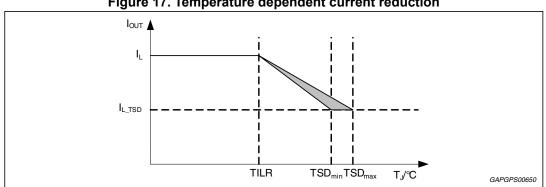
The overcurrent threshold is not changed by RCF (see Table 16). The current limitation is active as long as the output driver is switched on. The information that the device is in current limitation is stored in the diagnosis register 2 (DIA\_REG2).





#### 4.2.3 Temperature dependent current reduction

If the device reaches the temperature TILR, the current will be reduced (see Figure 17: Temperature dependent current reduction). If the temperature reaches the temperature shutdown threshold **TSD**, the outputs are switched off. The current limitation information is written into the diagnosis register 2 (DIA REG2).



### Figure 17. Temperature dependent current reduction



## 4.2.4 Short to battery (SCB) and short to Ground (SCG)

While the power stages are on, the current through them is monitored. If the output current reaches the current limit IL, the output is switched off after the blanking time  $t_b$ . In case the current reaches the limit  $I_{OC}$  during this time, a short to battery (SCB) on low-sides or a short to ground (SCG) on high-sides is diagnosed, and the affected output driver is switched off immediately, the not affected one after the time  $t_{DF}$  del.

In order to confirm this error, the outputs are turned on again. If the error is detected for the second time, it is confirmed but it is still not possible to determine to which of the following types belongs to:

- SCB and SCL
- SCG and SCL

To discriminate the fault type, it is necessary to turn outputs on for the third time, and in case the fault is detected, the diagnosis register (DIA\_REG1) is updated consequently and the device is disabled. Otherwise, the SCG and SCB faults are confirmed only.

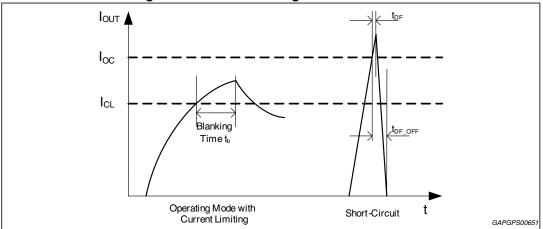


Figure 18. Current limiting and short circuit

The three different over-current limits are related to the programmable current limitation, which can be programmed into the SPI register (*Table 33: Configuration register* (*CONFIG\_REG*)). The over-current limits are independent of the resistor at pin CF.

*Note:* SCG: Fault Detection works correctly if the following condition is respected: Duty (switch on time) > Tdon + Slew rate + tDF.

## 4.2.5 Short circuit over load (SCL)

Short circuit over load (SCL) is diagnosed by a retest sequence after a short to battery (SCB) or a short to ground (SCG) has been detected and confirmed by a retry on the switched-on high-side and low-side driver. Then after the time  $t_{retest}$ , the opposite driver is switched off (i.e. the high-side in case of a short to battery on the low-side and vice versa). If the failure then disappears, a short over load (SCL) is detected.

The error is only entered into the diagnosis register and the device is disabled, if it is confirmed.



## 4.2.6 Open load (OL)

Open load can either be detected in active mode or while the output drivers are in a tri-state condition, disabled by DIS or /ABE. Open load in active mode is enabled by setting the **OLDA** in the configuration register (CONFIG\_REG).

### Open load in active mode

With OLDA = '1', the open load condition can only be diagnosed if an inductive load is used. In normal operation, the output free wheels via the built-in diodes below ground, if the highside output driver is switched-off. If the output does not go below ground, an open load is detected. It is possible to enable the filter OLDAFILTER by setting the dedicated bit 4 in SPECIAL\_REG (0 or 40ms). With OLDAFILTER = '1', the open-load will be recheck at the next PWM cycle and if detected again, the failure will be confirmed in DIAG\_REG1 (and latched).

In case OLDAFILTER is set at '0' (40ms) the recheck will be executed after the filter time expiration and next PWM pulse. If detected again, the failure will be confirmed (and latched).

Note: For Open-load in active mode L9959 works properly in case the duration of the transient conditions is less than 40msec (Transient condition: function of starting current, ending current, load electrical parameters, DC MOTOR mechanical characteristics...).

### Open load in inactive mode

In inactive mode the open load is independent from the OLDAFILTER status (don't care condition) and it is detected by applying a pull-down current ( $I_{PD}$ ) to both outputs. A pull-up current is generated at one output to compensate these two output currents. If the pull-up current is in the range of one pull-down current, an open load is diagnosed. If the load is connected, the pull up current is in the range of the sum of both pull-down currents.

An open load is detected, if the load resistance is above the open load resistance threshold; no open load is detected, if it is below this threshold ( $R_{OL}$ ).

After the outputs are disabled, it takes the time  $t_{DIAGOL}$  until the open load diagnostic can be enabled. The open load settling time to reach the correct pull up current is  $t_{diagOL1}$ , the open load filter time is  $t_{diagOL2}$ .

## 4.3 VS-undervoltage

VS is monitored for under-voltage. If VS goes below the VS-undervoltage threshold, the outputs are switched to tristate after the time  $t_{FUV}$ .

## 4.4 Inverse current at V<sub>S</sub>

An inverse current of maximum 5 A, which decreases during a period of max 250 ms out of the device at VS does not lead to any destruction. After the exposure to such an inverse current the device returns to the specified functionality.



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## 4.5 /ABE pin

/ABE (Ability/Enable) is a bidirectional pin, with an open-drain output. In normal operating condition, this pin is pulled up by an external resistor. If /ABE is set to low, the outputs enter tristate mode.

/ABE can be used to switch off the outputs quickly by an external signal. It is possible to connect the /ABE pins of several devices together, so all of them can be disabled in case one detects an error, which is flagged by the /ABE pin.

# 4.6 VDD-monitor

V<sub>DD</sub> is monitored for under- and over-voltage referenced to GND<sub>ABE</sub>.

If  $V_{DD}$  goes below  $V_{DD\_THL}$  or above  $V_{DD\_THH}$ , /ABE is pulled to low and the outputs enter tristate mode after the time  $t_{FIL\_OFF}$ . The VDD-monitoring state is stored into the status and control register (STACON\_REG).

If VDD increases above  $V_{DD_THL}$ , /ABE is pulled to high after the filter time  $t_{FIL_ON}$ . The SPI remains functional as long as  $V_{DD}$  is above the power-on reset threshold.

The behavior of the pin /ABE and the output stages after VDD goes below **VDD\_THH** from VDD-over-voltage is determined by bit CONFIG 0 in the status and configuration register (STATCON):

CONFIG0 = 1: /ABE is latched and the outputs remain in tristate

CONFIG0 = 0: /ABE goes to inactive and the output stages are enabled after the filtering time  $t_{FIL ON}$ .

# 4.7 VDD-monitor test

VDD-Monitor blocks can be tested in the application via SPI. During this test, the output stages are still switched off in case of over- and under-voltage.

### **Upper threshold**

The over-voltage threshold can be reduced using the configuration registers 1 and 2 (CONFIG1 and CONFIG2) in the status and control register (STACON\_REG) to **V**<sub>TEST\_THH</sub> (see *Table 35: Status and configuration register (STATCON\_REG)*). Since **V**<sub>TEST\_THH</sub> is below the normal VDD voltage, the status bit STATUS0 shows a VDD over-voltage.

### Lower threshold

The under-voltage threshold can be increased to  $V_{TEST_THL}$  using CONFIG1 and CONFIG2 in the STATCON register. Since the VDD voltage is below  $V_{TEST_THL}$ , the resulting VDD-undervoltage resets STATUS0.

After leaving the VDD-monitor test mode, the bits in the STACON register return to their normal state.



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## 4.8 **Power-on reset**

At power-on, while VDD increases, the internal registers are cleared and the outputs are set to tristate at the reset-active voltage  $V_{DDRES}$ . Above the power-on reset threshold  $V_{DDPOR}$  the device starts to operate after the time  $t_{POR}$ . If VDD drops below  $V_{DDPOR}$ , the device enters its reset state, i.e. all internal registers are cleared and the outputs are set to tristate.

V <sub>S</sub> [V]	V <sub>DD</sub> [V]	Functional state
28 – 40	0 – 18	No damage to the device, no functional behavior guaranteed
4.5 - 6.5	4.5 - 5.5	Device functional, Current Feedback accuracy reduced
6.5 – 28	4.5 – 5.5	Device functional
4.5 – 28	4.0 – 4.5 5.5 - 18	Device functional, but power-outputs tristate by VDD-monitor, /ABE pulled to low, SPI functional
0-4.54.5-28	VDD <sub>POR</sub> – 4.5	Device in reset mode, SPI functional, power-outputs tristate, /ABE pulled to low
0-4.54.5-28	2.5 - VDD <sub>POR</sub>	Device in reset mode, SPI reset, power-outputs tristate, /ABE tristate
0-4.5	4.5 – 5.5	Device functional, outputs are tristate by Vs-undervoltage
0 - 4.5	4.0 – 4.5 5.5 - 18	Device functional, outputs are tristate by Vs-undervoltage and V_DD-monitor, /ABE pulled to low

Note: All voltages are nominal. Please refer to Section 3: Electrical specifications for their specified values.



# 5 SPI functional description

## 5.1 General description

The SPI communication is based on a Serial Peripheral Interface structure using SS (SPI Select), SI (Serial Data In), SO (Serial Data Out) and SCK (Serial Clock) signal lines. The first data at pin SI is latched into the device with the first falling edge of the clock SCK after the clock has changed from low to high, which is the second edge after SPI-Select has been pulled to low.

### 5.1.1 SPI select (SS)

The SS input pin is used to select the serial interface of this device. When SS is high, the output pin (SO) is in high impedance state. A low signal starts the serial communication. A communication frame is the time between the falling edge of SS and its rising edge.

### 5.1.2 Serial data In (SI)

The SI input pin is used to transfer data serially into the device. The data applied to the SI is sampled at the falling edge of the SCK signal.

### 5.1.3 Serial clock (SCK)

The Data Input (SI) is latched at the falling edge of Serial Clock SCK. Data on Serial Data Out (SO) is shifted out at the rising edge of the serial clock (SCK). The serial clock SCK must be active only during a frame (SS low).

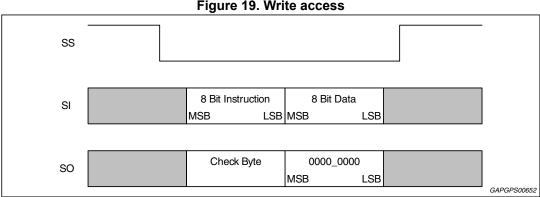
### 5.1.4 Serial out (SO)

The content of the selected status or control register is transferred out of the device using the SO pin on the rising edge of SCK. Each subsequent rising edge of the SCK will shift the next bit out.

### 5.1.5 SPI communication flow

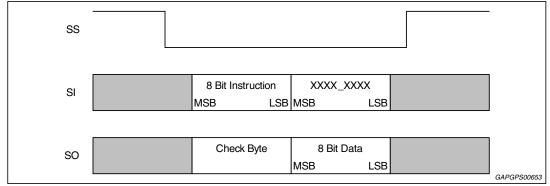
The SPI communication is started by sending an SPI instruction to the device beginning with the MSB. The first two bits of this instruction are used as a device identifier (see Table 24: SPI instruction byte). Whether the transfer is a read or a write access is determined by the SPI command (see Table 26: Command overview). The SPI data is transmitted from the device at the same time as the data is received, although on different SCK edges. While the 8-bit instruction is sent, the device responds with the check byte. Since the first two bits of the instruction are used as a device identifier, the first two bits of the check byte are tristate. This avoids bus conflicts on the SO line. During a write access, the 8-bit data byte is received after the instruction byte. The device responds with **00<sub>H</sub>**. In a read cycle the device sends the 8-bit data, while the receive data bits are ignored (see Figure 19: Write access and Figure 20: Read access). If an invalid instruction is detected, the register of the device are not modified and the data byte  $FF_H$  is transmitted instead of the data or  $00_H$  respectively. The bit **TRANS\_F** in the check byte is set in case of an invalid instruction and transmitted during the next SPI-access. An instruction is invalid, if an unused instruction code is detected, the previous transmission has not been completed or the number of clocks is not equal to 16.





### Figure 19. Write access

### Figure 20. Read access



#### 5.2 **SPI-instruction**

Table 24. SPI instruction byte

Bit	7	6	5	4	3	2	1	0
Name	CPAD1	CPAD0	INST<5>	INST<4>	INST<3>	INST<2>	INST<1>	INST<0>
Bit	Name	Content	ontent					
7	CPAD1	Chip Addres	s: 0					
6	CPAD0	Chip Addres	s: 0					
5	INST<5>	Read/Write:	ead/Write: Read: 0 Write: 1					
4:0	INST<4:0>	SPI Instructi	on					



Bit	7	6	5	4	3	2	1	0
Name	Tristate	Tristate	1	0	1	0	1	TRANS_F
Bit	Name	Content	ntent					
7:6	Tristate	Tristate						
6:1		Fix Content:	Content: 10101					
0	TRANS_F	Transfer-Fai	ilure Invalid ir	nstruction TR	ANS_F = 1			

### Table 25. Check byte

# 5.3 Device register map

### Table 26. Command overview

Command	INST<5:0>	Content
RD_ID	00_0100	Read Device ID
RD_REV	00_0110	Read Device Revision
RD_DIA1	01_0000	Read Diagnostic Information Register 1
RD_DIA2	01_1000	Read Diagnostic Information Register 2
RD_CONFIG	00_1000	Read Configuration
RD_STATCON	00_1100	Read VDD Monitoring Status
RD_SPECIAL	00_1110	Read information from SPECIAL
WR_DIA1	11_0000	Write to Diagnostic Information Register 1
WR_DIA2	11_1000	Write to Diagnostic Information Register 2
WR_CONFIG	10_1000	Write Configuration
WR_STATCON	10_1100	Write VDD Monitoring Status
WR_SPECIAL	10_1110	Write information to SPECIAL
All Other	-	Invalid Command: TRANS_F: 1



#### 5.4 SPI - control and status registers

					· · /			
Bit	7	6	5	4	3	2	1	0
Name	ID<7>	ID<6>	ID<5>	ID<4>	ID<3>	ID<2>	ID<1>	ID<0>
Bit	Name	Content						
7:0	ID<7:0>	Device ID: D	DFH					

### Table 27. Device identifier (ID)

### Table 28. Revision register (REV)

Bit	7	6	5	4	3	2	1	0		
Name	SWR<3>	SWR<2>	SWR<1>	SWR<0>	MSR<3>	MSR<2>	MSR<1>	MSR<0>		
Bit	Name	Content	Content							
7:4	SWR<3:0>	Software Re	oftware Revision: <b>0H</b>							
3:0	MSR<3:0>	Mask Set Ro	evision: <b>06H</b> (	1)						

1. Here below the Mask set revision: 00H - AA 01H - BA 02H - CA 03H - CB 04H - DA 05H - DB 06H - DC

### Table 29. DIA\_REG1

Bit	7	6	5	4	3	2	1	0	
Name	/ABE / DIS	ОТ	Res	Res	DIA21	DIA20	DIA11	DIA10	
Bit	Name	Content							
7	/ABE / DIS	-	H-bridge Disable: ), if /ABE = 0 or DIS = 1						
6	ОТ	Over tempe	rature: 0:OT,	1: no OT					
5:4	Reserved	0							
3	DIA21								
2	DIA20		to (Table 20:	Diagnosia hi		(1))			
1	DIA11	Diagnose bi	ts ( <i>Table 30:</i>	Diagnosis Di	IS (DIA_REG	())			
0	DIA10								
<b>Reset</b> <sup>(5.4.</sup> 1 <sup>)</sup>	7	6	5	4	3	2	1	0	
POR	Х	1	1	1	1	1	1	1	
SPIR	Х	1	Х	Х	1	1	1	1	
ENDISR	Х	1	Х	Х	1	1	1	1	
RDR	Х	Х	Х	Х	Х	Х	Х	Х	
DIACLR1	Х	1	Х	Х	1	1	1	1	



DIA21	DIA20	DIA11	DIA10	Description	Remark
0	0	0	1	Short Circuit to Ground at OUT1 (SCG1)	Latched
0	0	1	0	Short Circuit to Ground at OUT2 (SCG2)	Latched
0	1	0	1	Short Circuit to Battery at OUT1 (SCB1)	Latched
0	1	1	0	Short Circuit to Battery at OUT2 (SCB2)	Latched
0	1	1	1	Short Circuit over Load (SCL)	Latched
1	0	0	0	Short Circuit to Battery at Disabled Output	Latched
1	0	0	1	Short Circuit to Ground at Disabled Output	Latched
1	0	1	0	Open Load at disabled or active Output (OL)	Latched
1	1	0	1	Under Voltage at VS	Not Latched
1	1	1	1	No Failure	-

Table 30	Diagnosis	bits (		RFG1)
	Diagnosis	DILS	רייט)	

Note: Reading this register does not reset the bits. Writing STACON\_REG.DIACLR1 = 0 transfers all latched errors to DIA\_REG2 and resets DIA\_REG1 afterwards, if there is no VS-undervoltage.

Bit	7	6	5	4	3	2	1	0	
Name	CurrRed	CurrLim	ОТ	Res	DIA21	DIA20	DIA11	DIA10	
Bit	Name	Content							
7	CurrRed	Current Red 0, if tempera each read a	ature depend	ent current re	duction is ac	tive This info	rmation bit is	reset after	
6	CurrLim		Current Limitation: 0, if current limitation is active This information bit is reset after each read access						
5	ОТ	1 no over-te	Over temperature 1 no over-temperature 0 over-temperature						
4	Res	Reserved, 0							
3	DIA21								
2	DIA20			00. Dia					
1	DIA11	Diagnosis B	its (see <i>lable</i>	e 32: Diagnos	sis dits (DIA_I	REG2))			
0	DIA10								
<b>Reset</b> <sup>(5.4.</sup> 1 <sup>)</sup>	7	6	5	4	3	2	1	0	
POR	1	1	1	0	1	1	1	1	
SPIR	1	1	1	Х	1	1	1	1	
ENDISR	1	1	Х	Х	Х	Х	Х	Х	
RDR	1	1	Х	Х	Х	Х	Х	Х	
DIACLR2	1	1	1	Х	1	1	1	1	

Table 31. Diagnosis register 2 (DIA\_REG2)







DIA21	DIA20	DIA20 DIA11 DIA10 Description		Remark	
0	0	0	1	Short Circuit to Ground at OUT1 (SCG1)	Latched
0	0	1	0	Short Circuit to Ground at OUT2 (SCG2)	Latched
0	1	0	1	Short Circuit to Battery at OUT1 (SCB1)	Latched
0	1	1	0	Short Circuit to Battery at OUT2 (SCB2)	Latched
0	1	1	1	Short Circuit over Load (SCL)	Latched
1	0	0	0	Short Circuit to Battery at Disabled Output	Latched
1	0	0	1	Short Circuit to Ground at Disabled Output	Latched
1	0	1	0	Open Load at disabled or active Output (OL)	Latched
1	1	1	1	No Failure	-

Table 32. Diagnosis bits (DIA\_REG2)

Table 33. Configuration register (CONFIG\_REG)

Bit	7	6	5	4	3	2	1	0		
Name	FW	MUX	SPWM	SDIR	CL1	CL2	RESET	OLDA		
Bit	Name	Content								
7	FW		Free-Wheeling mode selection 0: FW via Body Diode; 1: FW with active short of Body Diode							
6	MUX		Multiplex Bit for H-bridge control strategy: 0: control by bits SPWM and SDIR; 1: Control by inputs PWM and DIR							
5	SDIR	SPI control f	for Direction:	Same as inp	ut DIR					
4	SPWM	SPI control f	for PWM: Sai	me as input F	PWM					
3	CL1	See Table 2	4: Current Le							
2	CL2	See Table 5	4. Current Le		<u>_REG</u> ).					
1	RESET	Reset: 0: Re	eset of device	configuratio	n to default; <sup>2</sup>	I: No change	;			
0	OLDA	Open-Load	Diagnosis in	active mode:	1: OLDA is e	enabled; 0: O	LDA is disab	led		
<b>Reset</b> <sup>(5.4.</sup>	7	6	5	4	3	2	1	0		
POR	1	1	1	1	1	0	1	0		
SPIR	1	1	1	1	1	0	1	0		
ENDISR	Х	X	Х	Х	Х	Х	1	Х		
RDR	Х	X	Х	Х	Х	Х	1	Х		



CL1	CL2	Current Level	Typical Current					
0	0	No Change	No Change					
0	1	2	5.0 A					
1	0	3 (default value)	6.6 A					
1	1	4	8.6 A					

Table 34.	<b>Current Level</b>	(CONFIG	REG)

Bit	7	6	5	4	3	2	1	0
Name	CONFIG2	CONFIG1	CONFIG0	DIACLR2	DIACLR1	STATUS2	STATUS1	STATUS0
Bit	Name	Content					•	
7	CONFIG2	VDD Test Th 0: VDD Thre	nreshold: eshold Test is	on 1: VDD T	hreshold test	t is off		
6	CONFIG1	VDD Test Th 1: Lower VD	hreshold: D Test Thres	hold is lifted	0:Upper VDE	) Test Thresh	old is lowere	d
5	CONFIG0	VDD Over-V	/oltage Latch	: 0: Latch is c	lisabled 1: La	atch is enable	ed	
4	DIACLR2	Reset DIA_I 0: Reset err	REG2: ors in DIA_R	EG2 1: No ac	tion (Readin	g this bit alwa	ays returns "1	.)
3	DIACLR1	0: All latched DIA10are se	Transfer Errors: 0: All latched errors of DIA_REG1 are transferred to DIA_REG2. DIA21,DIA20, DIA11, DIA10are set to "1111". During VS-Undervoltage DIACLR1 is disabled 1: No action (Reading this bit always returns _1.)					
2	STATUS2	Logic Level	at Pin /ABE					
1	STATUS1	VDD Under- 0: Under-Vo 1: No Under	ltage					
0	STATUS0	VDD Over-Voltage: 0: Over-Voltage 1: No Over-Voltage This information is not reset during VS-Undervoltage. It will be reset by CONFIG0, reset or internal VDD reset					FIG0, SPI	
Reset <sup>(5.4.1)</sup>	7	6	5	4	3	2	1	0
POR	1	1	0	1	1	Х	х	х
SPIR	1	1	0	1	1	Х	Х	Х
ENDISR	Х	Х	Х	1	1	Х	Х	Х
RDR	Х	Х	Х	1	1	Х	Х	Х

Note: Only the bits 'CONFIG' and 'DIACLR' in this register can be written, all other bits are 'readonly'



Table 36. Special register (SPECIAL_REG)								
Bit	7	6	5	4	3	2	1	0
Name		Not specified		OLDAFILT ER	Not specified	SR	Not specified	SPRCSPE C
Controller a	iccess:							
		s: WR_SPEC s: RD_SPECI						
Bit	Name	Content						
7	Not specified	-						
6	Not specified	-						
5	Not specified	-						
4	OLDAFILT ER	OLDAFILTE 1: open-load	I in on detect	mode only. care in case c ed after one ed after 40 m	retry			
3	Not specified	-						
2	SR	Voltage SR 1: fast slew 0: slow slew	rate					
1	Not specified	-						
0	SPRCSPE C	SPREADSPECTRUM mode selection         1: spread spectrum = active         0: spread spectrum = disabled         Spread spectrum = active provides the internal state machine with slightly tittering         Spread spectrum = disabled.         The internal state machine runs with constant clock         frequency.					-	
Reset ( <u>5.4.1</u> )	7	6	5	4	3	2	1	0
POR	0	0	0	1	0	0	0	1
SPIR	0	0	0	1	0	0	0	1
ENDISR	Х	Х	Х	X	Х	Х	X	X
RDR	Х	X	Х	X	Х	х	x	X

Table 36. Special register (SPECIAL\_REG)



### 5.4.1 Reset sources

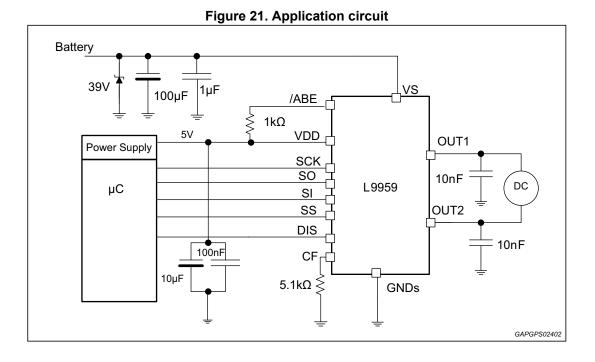
- POR: Reset due to a VDD power up on VDD (Power-Up Reset)
- ENDISR: Reset caused by an enable or disable of the power stages (DIS or /ABE edge triggered) (Enable-/Disable Reset)

### 5.4.2 Configuration registers reset sources

- POR: Reset due to a VDD power up on VDD (Power-Up Reset)
- SPIR: Reset by setting bit **RESET** in the configuration register (CONFIG\_REG) (SPIReset)
- RDIR: Reset caused by a read access to the corresponding register (Read Register)
- DIACLR1: Reset by setting bit DIACLR1 in the Status and Configuration Register STATCON (Diagnosis Reset 1)
- DIACLR2: Reset by setting bit DIACLR2 in the Status and Configuration Register STATCON (Diagnosis Reset 2)



# 6 Application circuit



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## 7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: *www.st.com*.

ECOPACK<sup>®</sup> is an ST trademark.

## 7.1 PowerSSO-24 (exposed pad) package information

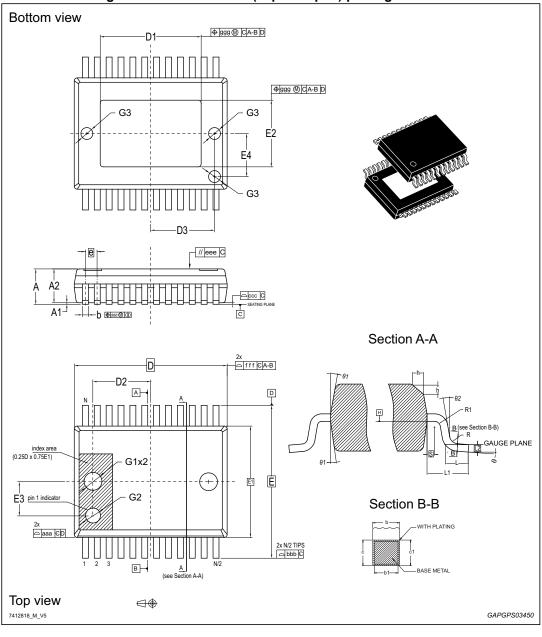


Figure 22. PowerSSO-24 (exposed pad) package outline



	ble 37. PowerSSO-24 (exposed pad) package mechanical data Dimensions							
Ref		Millimeters			Inches <sup>(1)</sup>			
	Min.	Тур.	Max.	Min.	Тур.	Max.		
θ	0°	-	8°	0°	-	8°		
θ1	5°	-	10°	5°	-	10°		
θ2	0°	-	-	0°	-	-		
А	-	-	2.45	-		0.0965		
A1	0.0	-	0.1	0.0		0.0039		
A2	2.15	-	2.35	0.0846		0.0925		
b	0.33	-	0.51	0.013		0.0201		
b1	0.28	0.40	0.48	0.011	0.0157	0.0189		
С	0.23	-	0.32	0.0091		0.0126		
c1	0.20	0.20	0.30	0.0079	0.0079	0.0118		
D <sup>(2)</sup>		10.30 BSC			0.4055 BSC			
D1			VARI	ATION				
D2	-	3.65	-	-	0.1437	-		
D3	-	4.30	-	-	0.1693	-		
е		0.80 BSC		0.0315 BSC				
E		10.30 BSC		0.4055 BSC				
E1 <sup>(2)</sup>		7.50 BSC		0.2953 BSC				
E2			VARI	ATION				
E3	-	2.30	-	-	0.0906	-		
E4	-	2.90	-	-	0.1142	-		
G1	-	1.20	-	-	0.0472	-		
G2	-	1.0	-	-	0.0394	-		
G3	-	0.80	-	-	0.0315	-		
h	0.30	-	0.40	0.0118	-	0.0157		
L	0.55	0.70	0.85	0.0217	-	0.0335		
L1		1.40 REF			0.0551 REF			
L2	0.25 BSC				0.0098 BSC			
N			24 (#	ŧlead)				
R	0.30	-	-	0.0118	-	-		
R1	0.20	-	-	0.0079	-	-		
S	0.25	-	-	0.0098	-	-		

### Table 37. PowerSSO-24 (exposed pad) package mechanical data



	· · ·						
Ref		Millimeters			nsions Inches <sup>(1)</sup>		
	Min.	Тур.	Max.	Min.	Тур.	Max.	
	I	Toleranc	e of form an	d position	1	1	
aaa		0.20			0.0079		
bbb		0.20			0.0079		
ссс		0.10			0.0039		
ddd		0.20		0.0079			
eee		0.10		0.0039			
ffff		0.20		0.0079			
<u>ggg</u>		0.15		0.0059			
	•		VARIATIONS	6			
Option A							
D1	6.5	-	7.1	0.2559	-	0.2795	
E2	4.1 - 4.7			0.1614 -			
Option B							
D1	4.9	-	5.5	0.1929	-	0.2165	
E2	4.1	-	4.7	0.1614	-	0.1850	

Table 37. PowerSSO-24 (exposed pad) package mechanical data (continued)

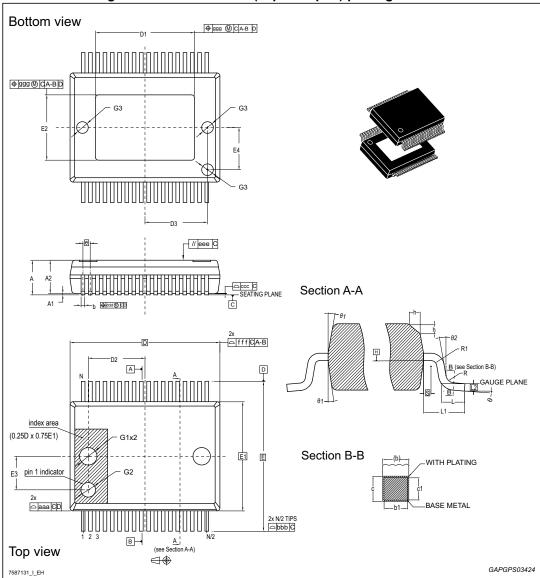
1. Values in inches are converted from mm and rounded to 4 decimal digits.

 Dimensions D and E1 do not include mold flash or protrusions. Allowable mold flash or protrusions is '0.25 mm' per side D and '0.15 mm' per side E1. D and E1 are Maximum plastic body size dimensions including mold mismatch.



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## 7.2 PowerSSO-36 (exposed pad) package information



#### Figure 23. PowerSSO-36 (exposed pad) package outline



	Dimensions							
Ref		Millimeters		Inches <sup>(1)</sup>				
	Min.	Тур.	Max.	Min.	Тур.	Max.		
θ	0°	-	8°	0°	-	8°		
θ1	5°	-	10°	5°	-	10°		
θ2	0°	-	-	0°	-	-		
A	2.15	-	2.45	0.0846	-	0.0965		



		Dimensions							
Ref		Millimeters			Inches <sup>(1)</sup>				
	Min.	Тур.	Max.	Min.	Тур.	Max.			
A1	0.0	-	0.1	0.0	-	0.0039			
A2	2.15	-	2.35	0.0846	-	0.0925			
b	0.18	-	0.32	0.0071	-	0.0126			
b1	0.13	0.25	0.3	0.0051	0.0098	0.0118			
С	0.23	-	0.32	0.0091	-	0.0126			
c1	0.2	0.2	0.3	0.0079	0.0079	0.0118			
D <sup>(2)</sup>		10.30 BSC			0.4055 BSC	•			
D1			VAR	ATION					
D2	-	3.65	-	-	0.1437	-			
D3	-	4.3	-	-	0.1693	-			
е		0.50 BSC			0.0197 BSC	1			
E		10.30 BSC		0.4055 BSC					
E1 <sup>(2)</sup>		7.50 BSC		0.2953 BSC					
E2			VAR	IATION					
E3	-	2.3	-	-	0.0906	-			
E4	-	2.9	-	-	0.1142	-			
G1	-	1.2	-	-	0.0472	-			
G2	-	1	-	-	0.0394	-			
G3	-	0.8	-	-	0.0315	-			
h	0.3	-	0.4	0.0118	-	0.0157			
L	0.55	0.7	0.85	0.0217	-	0.0335			
L1		1.40 REF			0.0551 REF	1			
L2		0.25 BSC		0.0098 BSC					
Ν		36			1.4173				
R	0.3	-	-	0.0118	-	-			
R1	0.2	-	-	0.0079	-	-			
S	0.25	-	-	0.0098	-	-			
	1	Tolerance	e of form and	d position	1	1			
aaa		0.2			0.0079				
bbb		0.2		0.0079					
CCC		0.1			0.0039				
ddd		0.2			0.0079				

 Table 38. PowerSSO-36 (exposed pad) package mechanical data (continued)

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	Dimensions								
Ref		Millimeters			Inches <sup>(1)</sup>				
	Min.	Тур.	Max.	Min.	Тур.	Max.			
eee		0.1	•		0.0039				
ffff		0.2			0.0079				
<u>ggg</u>		0.15			0.0059				
			VARIATIONS	5					
Option A									
D1	6.5	-	7.1	0.2559	-	0.2795			
E2	4.1	-	4.7	0.1614	-	0.1850			
Option B		•	•	•					
D1	4.9	-	5.5	0.1929	-	0.2165			
E2	4.1	-	4.7	0.1614	-	0.1850			
Option C				•					
D1	6.9	-	7.5	0.2717	-	0.2953			
E2	4.3	-	5.2	0.1693	-	0.2047			

### Table 38. PowerSSO-36 (exposed pad) package mechanical data (continued)

1. Values in inches are converted from mm and rounded to 4 decimal digits.

 Dimensions D and E1 do not include mold flash or protrusions. Allowable mold flash or protrusions is '0.25 mm' per side D and '0.15 mm' per side E1. D and E1 are Maximum plastic body size dimensions including mold mismatch.



# 8 Revision history

Date	Revision	Changes	
27-Jul-2015	1	Initial release.	
28-Oct-2015	2	<ul> <li>Added:</li> <li>New commercial part number in <i>Table 1: Device summary on</i> page 1;</li> <li><i>Figure 4: PSSO36 (Single version) pin connection (top view) on</i> page 8;</li> <li><i>Table 4: L9959U (Single version in PSSO36) pin out on page 12.</i></li> <li>Corrected in <i>Table 10: VDD monitoring on page 15</i> the test conditions of V<sub>ABE_OUTL</sub>.</li> <li>Updated <i>Description on page 1.</i></li> </ul>	
25-Feb-2016	3	Corrected typo in the <i>Table 10: VDD monitoring on page 15</i> (Test condition column of the 'V <sub>ABE_OUTL</sub> ' parameter).	

### Table 39. Document revision history

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